MOSFETs Silicon P-Channel MOS (U-MOSVI)

TJ200F04M3L

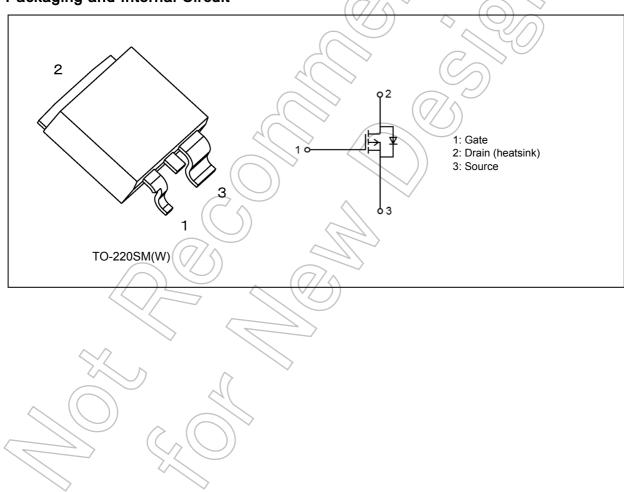
1. Applications

- Automotive
- DC-DC Converters
- Motor Drivers

2. Features

- (1) AEC-Q101 qualified
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 1.45 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -40 \ V)$
- (4) Enhancement mode: $V_{th} = -2.0$ to -3.0 V ($V_{DS} = -10$ V, $I_D = -1$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteri	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	-40	V
Gate-source voltage			V _{GSS}	-20/+10	
Drain current (DC)		(Note 1)	ID C	-200	A
Drain current (pulsed)		(Note 1)	I _{DP}	-600	
Power dissipation	(T _c = 25°C)	(Note 2)	PD	375	W
Single-pulse avalanche energy		(Note 3)	E _{AS}	924	mJ
Single-pulse avalanche current			I _{AS}	-200	A
Channel temperature		(Note 4)	T _{ch}) 175	°C
Storage temperature		(Note 4)	T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.4	°C/W

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: The power dissipation value is calculated based on the channel-to-case thermal resistance. However, the safe operating area is not only limited to thermal limits but also the current concentration phenomenon. This device should not be used under conditions outside its safe operating area shown herein.

Note 3: V_{DD} = -25 V, T_{ch} = 25°C (initial), L = 24 µH, R_G = 25 Ω, I_{AS} = -200 A, V_{GS} = 0/-15 V

Note 4: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V _{GS} = -20/+10 V, V _{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	$V_{DS} = -40 V, V_{GS} = 0 V$	J	_	-10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = -10 mA, V _{GS} = 0 V	-40		—	V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = -10 mA, V _{GS} = 10 V	-30	$\langle \gamma \rangle$	_	
Gate threshold voltage	V _{th}	V _{DS} = -10 V, I _D = -1 mA	-2.0	2_	-3.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = -6 V, I _D = -100 A	γ	1.74	2.6	mΩ
		V _{GS} = -10 V, I _D = -100 A	Ì	1.45	1.8	

Note 5: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz)(12800) —	pF
Reverse transfer capacitance	C _{rss}		\mathcal{A}	1150		
Output capacitance	C _{oss}		\sim	2400	_	
Switching time (rise time)	tr	See Fig. 6.2.1	Z))	14	—	ns
Switching time (turn-on time)	t _{on}		\sim	29	_	
Switching time (fall time)	t _f))—	515	_	
Switching time (turn-off time)	t _{off}		_	1750	_	

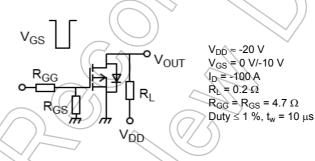


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

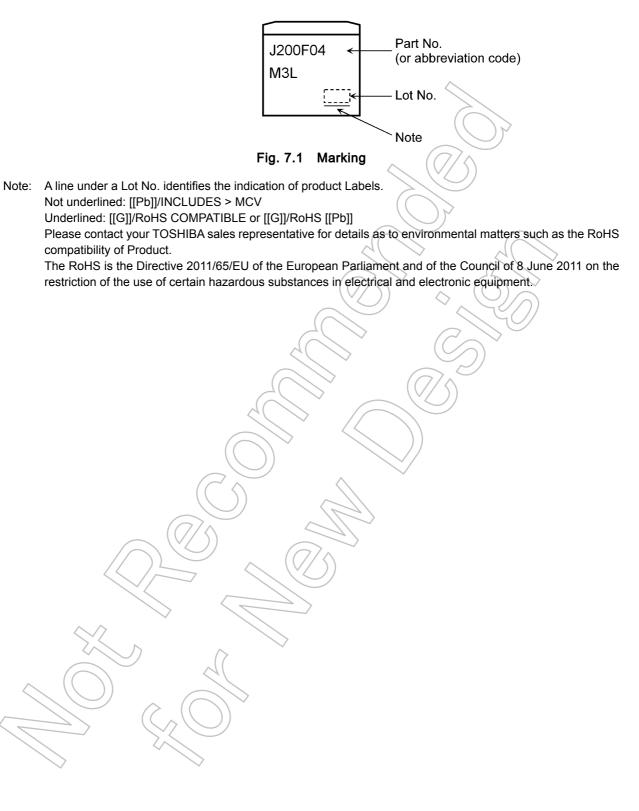
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx$ -32 V, V_{GS} = -10 V, I_D = -200 A	—	460	_	nC
Gate-source charge 1	Q _{gs1}		_	72	_	
Gate-drain charge	Q _{gd}		_	130	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 6)	I _{DR}	—	_	_	-200	Α
Reverse drain current (pulsed)	(Note 6)	I _{DRP}		_	_	-600	
Diode forward voltage		V _{DSF}	I _{DR} = -200 A, V _{GS} = 0 V	_	_	1.2	V
Reverse recovery time		t _{rr}	I _{DR} = -200 A, V _{GS} = 0 V	_	90	_	ns
Reverse recovery charge		Q _{rr}	dl _{DR} /dt = 50 A/µs	_	104	—	nC

Note 6: Ensure that the channel temperature does not exceed 175°C.

7. Marking (Note)



8. Moisture-Proof Packing

This device is packed in a moisture-proof laminated aluminum bag.

8.1. Precautions for Transportation and Storage (Note)

- (1) Avoid excessive vibration during transportation.
- (2) Do not toss or drop the packed devices to avoid ripping of the bag.
- (3) After opening the moisture-proof bag, the devices should be assembled within two weeks in an environment of 5°C to 30°C and RH70% or below. Perform reflow at most twice.
- (4) The moisture-proof bag may be stored unopened for up to 24 months at 5°C to 30°C and RH90% or below.
- (5) If, upon opening the bag, the moisture indicator card shows humidity of 30% or above (the color of the 30% dot has changed from blue to pink) or the expiration date has passed, the devices should be baked as follows:

Baking conditions: 125°C for 48 hours.

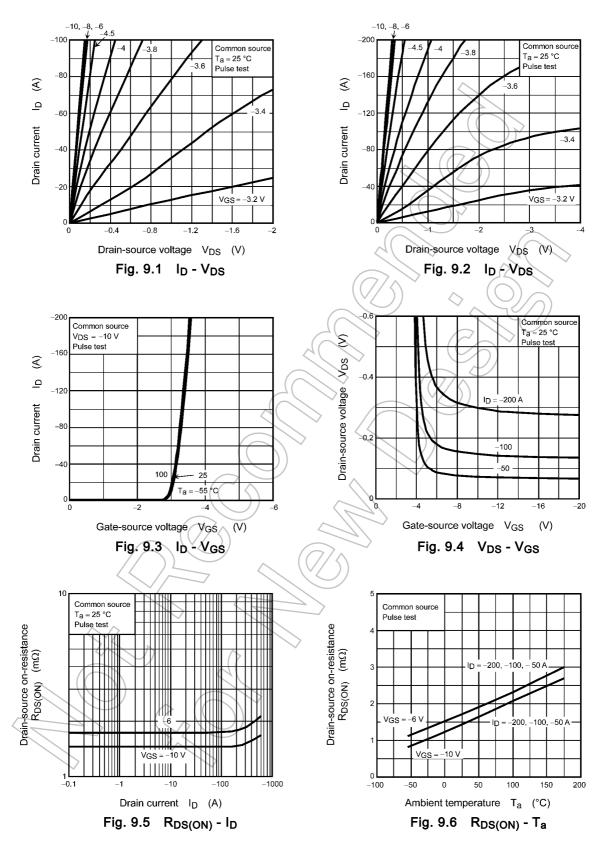
Note: Since the tape materials are not heat-proof, devices should be placed on either heat-proof trays or aluminum magazines when baking.

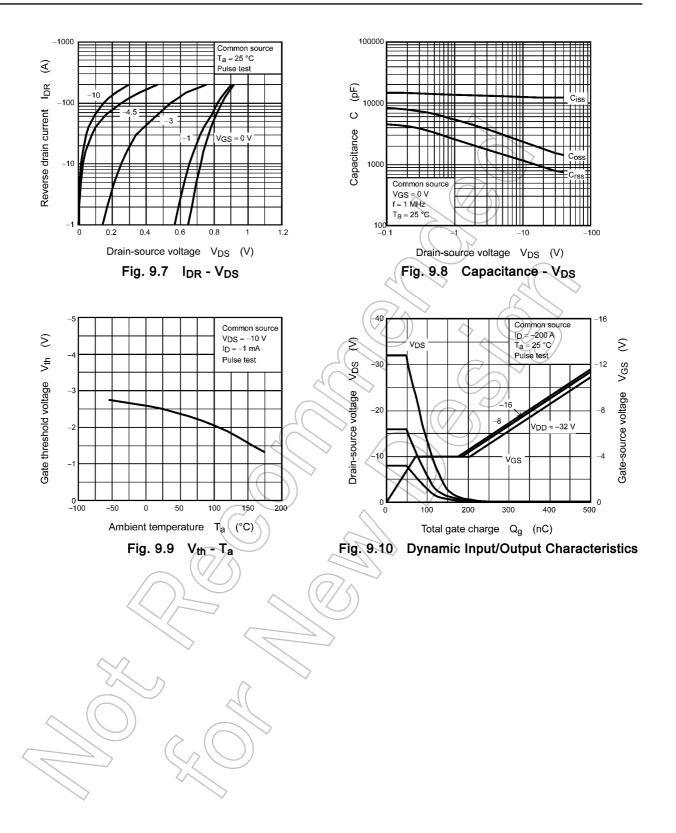


The humidity indicator shows an approximate ambient humidity at $25 \,$ °C. If the ambient humidity is below 30 %, the color of all the indicator dots is blue. If, upon opening the bag, the color of the 30 % dot has changed from blue to pink, the devices should be baked before assembly.

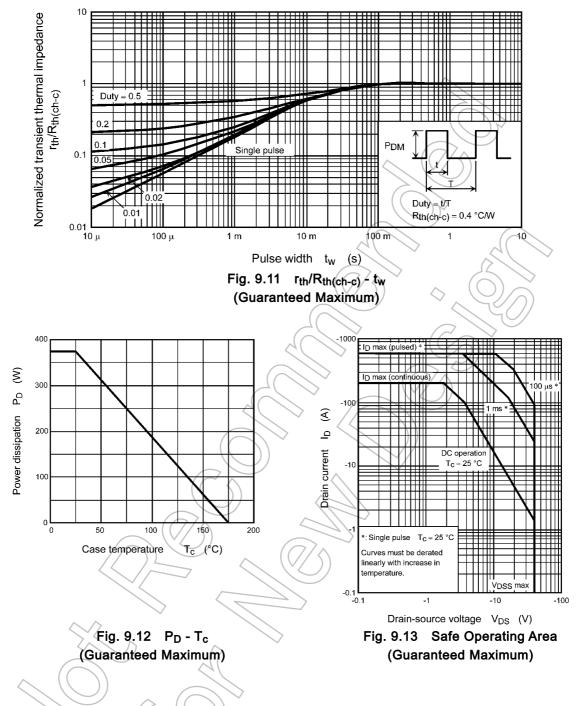
Fig. 8.1.1 Humidity Indicator

9. Characteristics Curves (Note)





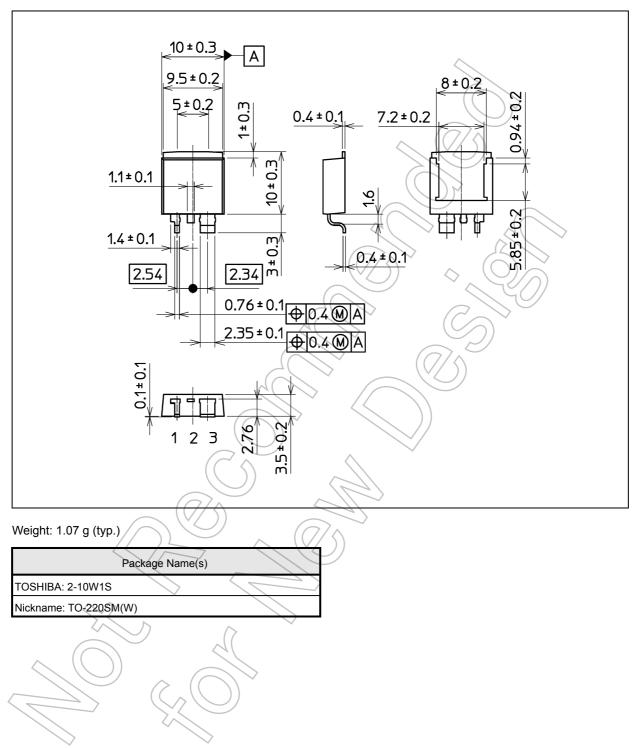




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



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